



STU7NA80

N - CHANNEL 800V - 1.3Ω - 6.5A - Max220 FAST POWER MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STU7NA80	800 V	< 1.5 Ω	6.5 A

- TYPICAL R_{DS(on)} = 1.3 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- REPETITIVE AVALANCHE TESTED DATA AT 100 °C
- LOW INTRINSIC CAPACITANCE
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- REDUCED THRESHOLD VOLTAGE SPREAD

DESCRIPTION

The Max220™ package is a new high volume power package exhibiting the same footprint as the industry standard TO-220, but designed to accommodate much larger silicon chips, normally supplied in bigger packages. The increased die capacity makes the device ideal to reduce component count in multiple paralleled TO-220 designs and save board space with respect to larger packages.

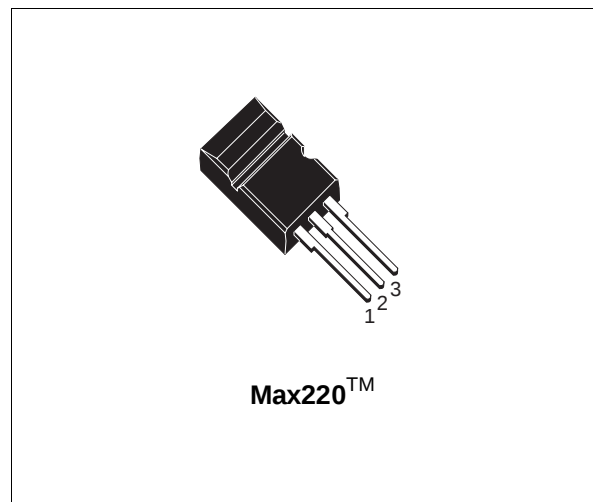
APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CONSUMER AND INDUSTRIAL LIGHTING
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES (UPS)

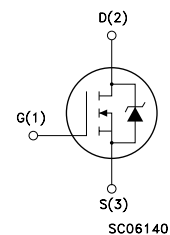
ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	800	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	800	V
V _{GS}	Gate-source Voltage	± 30	V
I _D	Drain Current (continuous) at T _c = 25 °C	6.5	A
I _D	Drain Current (continuous) at T _c = 100 °C	4.3	A
I _{DM} (•)	Drain Current (pulsed)	26	A
P _{tot}	Total Dissipation at T _c = 25 °C	145	W
	Derating Factor	1.16	W/°C
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area



INTERNAL SCHEMATIC DIAGRAM



THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	0.86	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	30	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.1	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	6.5	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	220	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA V _{GS} = 0	800			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating x 0.8 T _c = 100 °C			250 1000	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 30 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	2.25	3	3.75	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 3.5 A		1.3	1.5	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	6.5			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 3.5 A	4.5	7.2		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		1770	2300	pF
C _{oss}	Output Capacitance			190	250	pF
C _{rss}	Reverse Transfer Capacitance			50	70	pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 400\text{ V}$ $I_D =$		20	30	ns
t_r	Rise Time	3.5 A $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		30	45	ns
Q_g	Total Gate Charge	$V_{DD} = 480\text{ V}$ $I_D = 8\text{ A}$ $V_{GS} = 10\text{ V}$		75	110	nC
Q_{gs}	Gate-Source Charge			10		nC
Q_{gd}	Gate-Drain Charge			34		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 640\text{ V}$ $I_D = 7\text{ A}$		18	27	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		20	30	ns
t_c	Cross-over Time			25	40	ns

SOURCE DRAIN DIODE

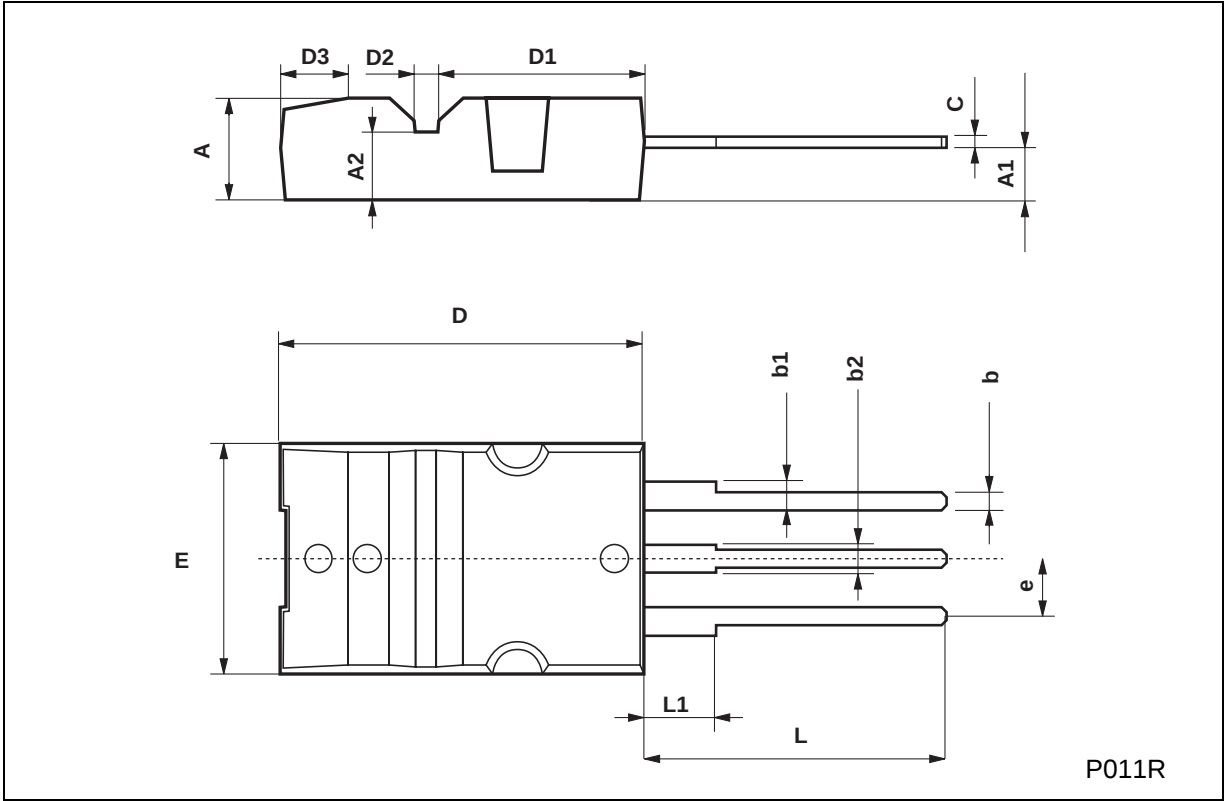
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				6.5	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				26	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 7\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 7\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		850		ns
Q_{rr}	Reverse Recovery Charge			17		μC
I_{RRM}	Reverse Recovery Current			40		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

Max220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.3		4.6	0.169		0.181
A1	2.2		2.4	0.087		0.094
A2	2.9		3.1	0.114		0.122
b	0.7		0.93	0.027		0.036
b1	1.25		1.4	0.049		0.055
b2	1.2		1.38	0.047		0.054
c	0.45		0.6		0.18	0.023
D	15.9		16.3		0.626	0.641
D1	9		9.35	0.354		0.368
D2	0.8		1.2	0.031		0.047
D3	2.8		3.2	0.110		0.126
e	2.44		2.64	0.096		0.104
E	10.05		10.35	0.396		0.407
L	13.2		13.6	0.520		0.535
L1	3		3.4	0.118		0.133



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